

## Amendment to the Specification

- 1) Please replace the sentence and Abstract beginning on page 20, with the following rewritten Abstract:

~~— Methods for producing silicon nitride films and silicon oxynitride films by thermal chemical vapor deposition~~

### Abstract

Silicon nitride film is formed on substrate (112) by feeding trisilylamine and ammonia into a CVD reaction chamber (11) that ~~holds~~ contains a substrate (112). ~~During this process,~~ the ammonia gas/trisilylamine gas flow rate ratio is set to a value of at least about 10 and/or the thermal CVD reaction is run at a temperature no greater than about 600°C. Silicon oxynitride is obtained by ~~also~~ introducing an oxygen source gas into the CVD reaction chamber (11). ~~The~~ This method ~~according to the invention~~ avoids the production of ammonium chloride and/or the incorporation of carbonaceous contaminants which are detrimental to the quality of the deposited film.

Figure --